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30V N-Channel Power MOSFET

TO-252 (DPAK)

2 650

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

Key Parameter Performance

Parameter		Value	Unit	
$V_{ t DS}$		30	V	
,	$V_{GS} = 10V$	6	mΩ	
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	9		
Q_g		11.1	nC	

Features

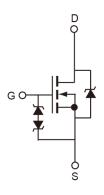
- Fast switching
- G-S ESD Protection Diode Embedded

Ordering Information

Part No.	Package	Packing		
TSM060N03ECP ROG	TO-252	2.5kpcs / 13" Reel		

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



N-Channel MOSFET with ESD protection

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		T _C =25ºC		70	Α
		T _C =100°C	l _D	44	Α
Pulsed Drain Current (Note 1)		I _{DM}	280	Α	
Single Pulse Avalanche Energy (Note 2)		E _{AS}	88	mJ	
Single Pulse Avalanche Current (Note 2)		I _{AS}	42	Α	
Total Power Dissipation	@ T _C =2	5°C	D	54	W
	Derate a	above T _C =25°C	P_{D}	0.43	W/ºC
Operating Junction Temperature		T _J	150	ōC	
Storage Temperature Range		T_{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\Theta JC}$	2.3	°C/W
Thermal Resistance - Junction to Ambient	R _{OJA}	62	°C/W



30V N-Channel Power MOSFET



Electrical Specifications (T_C=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				•	•	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 20A$	1		4.8	6	mΩ
	$V_{GS} = 4.5V, I_D = 10A$	$R_{DS(ON)}$		6.5	9	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1	1.6	2.5	٧
Zaus Cata Valtana Busin Commant	$V_{DS} = 30V, V_{GS} = 0V$				1	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 24V, T _J = 125 ^o C	I _{DSS}			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	μΑ
Forward Transconductance	$V_{DS} = 10V, I_{D} = 10A$	g _{fs}		12.5		S
Dynamic						
Total Gate Charge ^(Note 3,4)	$V_{DS} = 15V, I_{D} = 20A,$	Qg		11.1		nC
Gate-Source Charge ^(Note 3,4)		Q _{gs}		1.85		
Gate-Drain Charge ^(Note 3,4)	$V_{GS} = 4.5V$	Q_{gd}		6.8		
Input Capacitance		C _{iss}		1210		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1MHz	C _{oss}		190		pF
Reverse Transfer Capacitance	7 I = IIVIDZ	C _{rss}		100		-
Gate Resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz	R_g		2.5		Ω
Switching						
Turn-On Delay Time ^(Note 3,4)		t _{d(on)}		7.5		
Turn-On Rise Time ^(Note 3,4)	V _{DD} =15V , V _{GS} =10V ,	t _r		14.5		ns
Turn-Off Delay Time ^(Note 3,4)	$R_G=3.3\Omega$, $I_D=-15A$	t _{d(off)}		35.2		
Turn-Off Fall Time ^(Note 3,4)		t _f		9.6		
Source-Drain Diode Ratings and C	Characteristic	•				•
Continuous Drain-Source Diode	$V_G=V_D=0V$	Is			70	Α
Pulse Drain-Source Diode	Force Current	I _{SM}			280	Α
Diode-Source Forward Voltage	$V_{GS} = 0V$, $I_S = 1A$	V _{SD}			1	V
	•	•				•

Note:

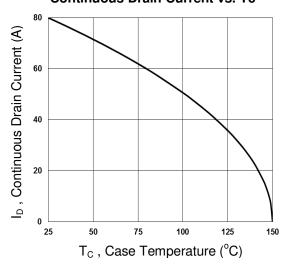
- 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2. V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =42A., R_{G} =25 Ω ,Starting T_{J} =25 $^{\circ}$ C
- 3. The data tested by pulsed , pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$
- 4. Essentially independent of operating temperature.



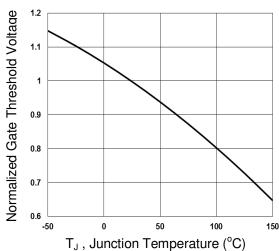
(Pb) RoHS

Electrical Characteristics Curve

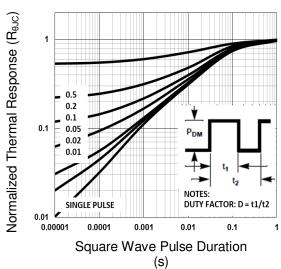
Continuous Drain Current vs. Tc



Normalized V_{th} vs. T_J

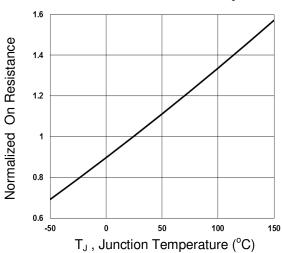


Normalized Transient Impedance

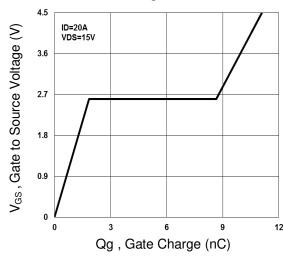


Normalized RDSON vs. T_J

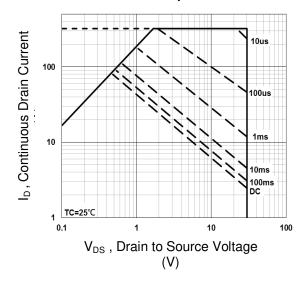
30V N-Channel Power MOSFET



Gate Charge Waveform



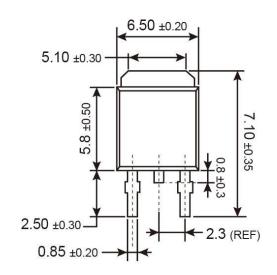
Maximum Safe Operation Area

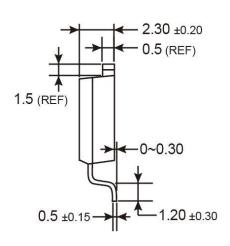




30V N-Channel Power MOSFET

TO-252 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: A14



TSM060N03ECP 30V N-Channel Power MOSFET

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